1. General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in industrial and communications applications.

2. Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for logic level gate drive sources

3. Applications

- Class-D amplifiers
- DC-to-DC converters
- Motor control
- Server power supplies

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	30	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	-	100	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	74	W
Static characte	eristics			•			'
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 ^{\circ}\text{C}$		-	2.43	3.5	mΩ
Dynamic chara	cteristics			•			
Q_{GD}	gate-drain charge	I _D = 10 A; V _{DS} = 12 V; V _{GS} = 4.5 V;		-	5	-	nC
Q _{G(tot)}	total gate charge	Fig. 14; Fig. 15		-	19	-	nC
Avalanche rug	gedness		•	•			
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I_D = 100 A; $V_{sup} \le 30$ V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped		-	-	54	mJ

[1] Continuous current is limited by package.



N-channel 30 V 3.5 m Ω logic level MOSFET in LFPAK

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source	<u> </u>	
3	S	source		G—(F)
4	G	gate	0.00	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PSMN3R5-30YL	'	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669		

7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN3R5-30YL	3R530

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	30	V
V _{DSM}	peak drain-source voltage	$t_p \le 25 \text{ ns}; f \le 500 \text{ kHz}; E_{DS(AL)} \le 180 \text{ nJ};$ pulsed		-	35	V
V_{DGR}	drain-gate voltage	$25 ^{\circ}$ C ≤ T _j ≤ 175 $^{\circ}$ C; R _{GS} = 20 kΩ		-	30	V
V _{GS}	gate-source voltage			-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	74	W
I _D	drain current	V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 2</u>	[1]	-	86	Α
		V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	100	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 °C$; Fig. 3		-	447	Α
T _{stg}	storage temperature			-55	175	°C
T _j	junction temperature			-55	175	°C
Source-drain	diode			'	•	
I _S	source current	T _{mb} = 25 °C	[1]	-	100	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	447	Α
Avalanche ru	ggedness			,		

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Symbol	Parameter	Conditions	Min	Max	Unit
DO(AL)O		I_D = 100 A; $V_{sup} \le 30$ V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped	-	54	mJ

[1] Continuous current is limited by package.

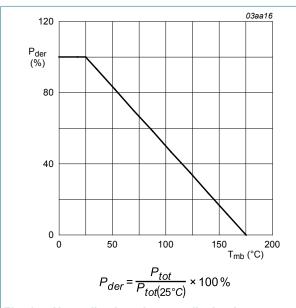
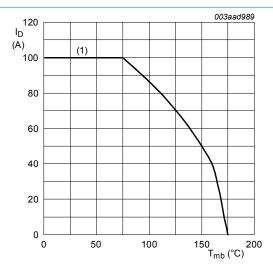


Fig. 1. Normalized total power dissipation as a function of mounting base temperature



 $V_{GS} \ge 10 \text{ V}$; (1) Capped at 100 A due to package

Fig. 2. Continuous drain current as a function of mounting base temperature

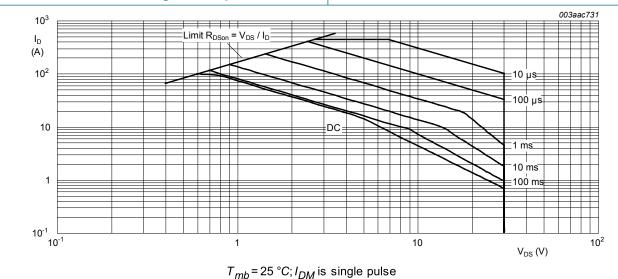


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
	thermal resistance from junction to mounting base	Fig. 4	-	0.6	1.68	K/W

(1) Capped at 100 A due to package.

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10. Characteristics

Table 7. Characteristics

Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics				_	
V _{(BR)DSS}	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	30	-	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	27	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}; Fig. 11; Fig. 12$	1.3	1.7	2.15	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 150 °C; Fig. 12	0.65	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}; Fig. 12$	-	-	2.45	V
I _{DSS}	drain leakage current	V _{DS} = 30 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μΑ
		V _{DS} = 30 V; V _{GS} = 0 V; T _j = 150 °C	-	-	100	μΑ
I _{GSS}	gate leakage current	V _{GS} = 16 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		V _{GS} = -16 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 4.5 V; I _D = 15 A; T _j = 25 °C	-	3.37	4.61	mΩ
		V _{GS} = 10 V; I _D = 15 A; T _j = 150 °C; Fig. 13	-	-	6	mΩ
		V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C	-	2.43	3.5	mΩ
R _G	gate resistance	f = 1 MHz	-	0.53	1.5	Ω
Dynamic ch	naracteristics		'			'
Q _{G(tot)}	total gate charge	I _D = 10 A; V _{DS} = 12 V; V _{GS} = 4.5 V; Fig. 14; Fig. 15	-	19	-	nC
		I _D = 0 A; V _{DS} = 0 V; V _{GS} = 10 V	-	37	-	nC
		I _D = 10 A; V _{DS} = 12 V; V _{GS} = 10 V; Fig. 14; Fig. 15	-	41	-	nC
Q _{GS}	gate-source charge	I _D = 10 A; V _{DS} = 12 V; V _{GS} = 4.5 V;	-	6	-	nC
Q _{GS(th)}	pre-threshold gate- source charge	Fig. 14; Fig. 15	-	4	-	nC

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Q _{GS(th-pl)}	post-threshold gate- source charge		-	2	-	nC
Q _{GD}	gate-drain charge		-	5	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	V _{DS} = 12 V; <u>Fig. 14</u> ; <u>Fig. 15</u>	-	2.4	-	V
C _{iss}	input capacitance	V _{DS} = 12 V; V _{GS} = 0 V; f = 1 MHz;	-	2458	3441	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 16</u>	-	532	718	pF
C _{rss}	reverse transfer capacitance		-	252	353	pF
t _{d(on)}	turn-on delay time	V_{DS} = 12 V; R_L = 0.5 Ω ; V_{GS} = 4.5 V;	-	33	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega$	-	50	-	ns
t _{d(off)}	turn-off delay time		-	45	-	ns
t _f	fall time		-	18	-	ns
Source-drai	in diode					
V _{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 17$	-	0.82	1.2	V
t _{rr}	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	37	-	ns
Q _r	recovered charge	V _{DS} = 20 V	-	31	-	nC

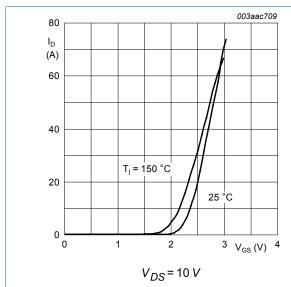


Fig. 5. Transfer characteristics: drain current as a function of gate-source voltage; typical values

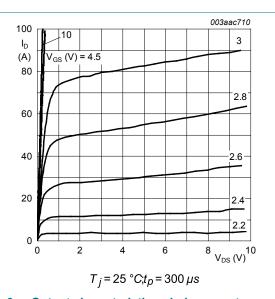


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

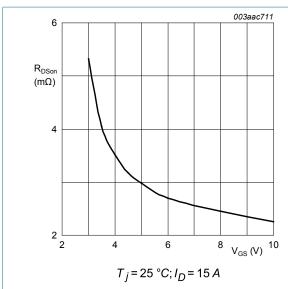


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

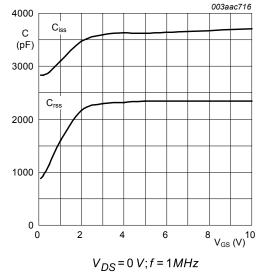


Fig. 8. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

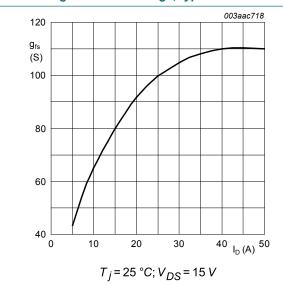


Fig. 9. Forward transconductance as a function of drain current; typical values

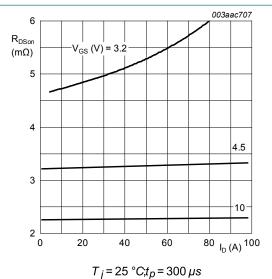


Fig. 10. Drain-source on-state resistance as a function of drain current; typical values

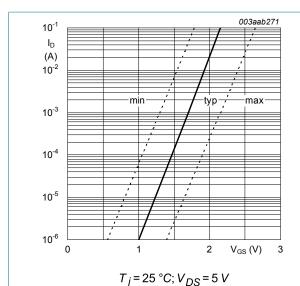


Fig. 11. Sub-threshold drain current as a function of gate-source voltage

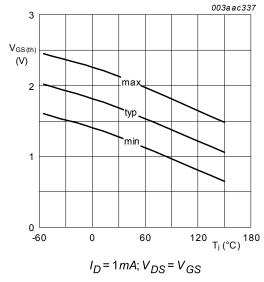


Fig. 12. Gate-source threshold voltage as a function of junction temperature

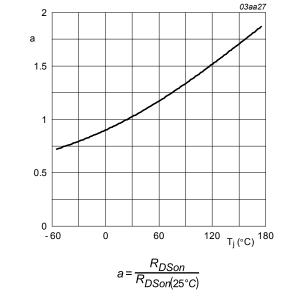


Fig. 13. Normalized drain-source on-state resistance factor as a function of junction temperature

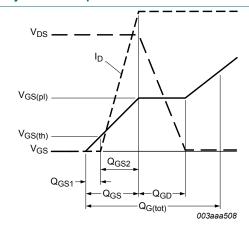


Fig. 14. Gate charge waveform definitions

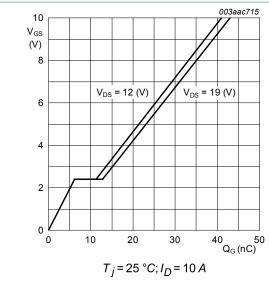


Fig. 15. Gate-source voltage as a function of gate charge; typical values

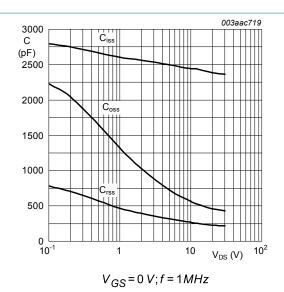


Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

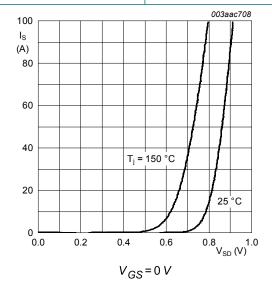


Fig. 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

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11. Package outline

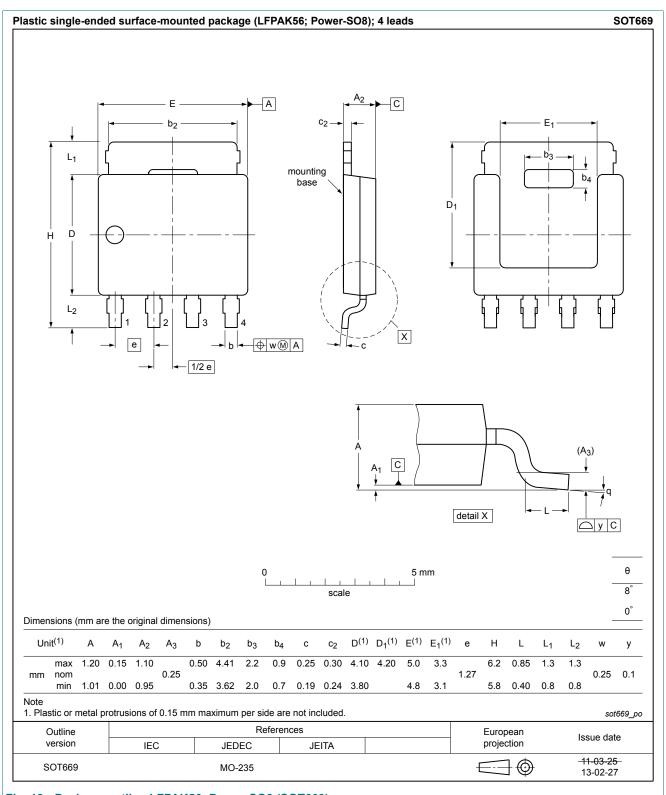
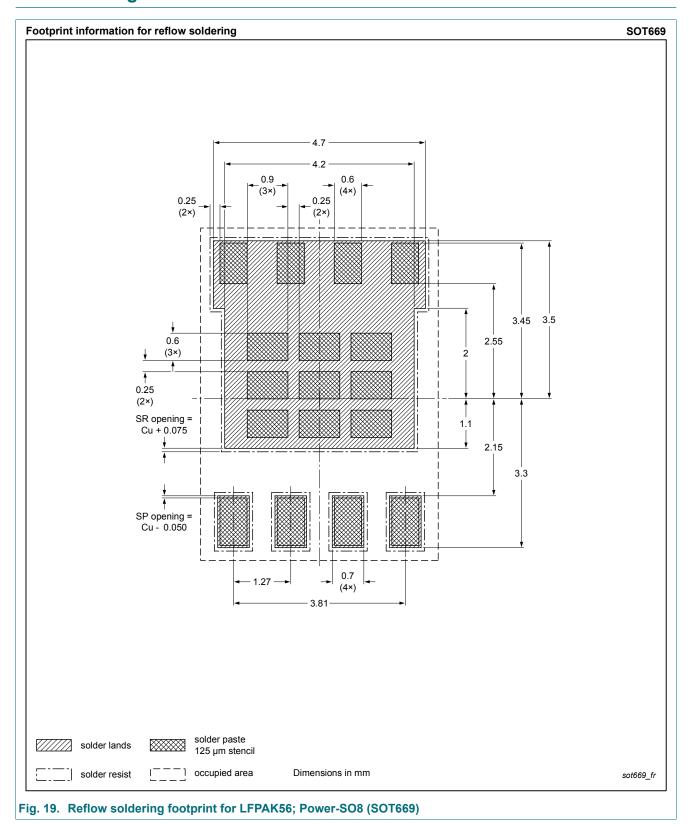


Fig. 18. Package outline LFPAK56; Power-SO8 (SOT669)

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12. Soldering



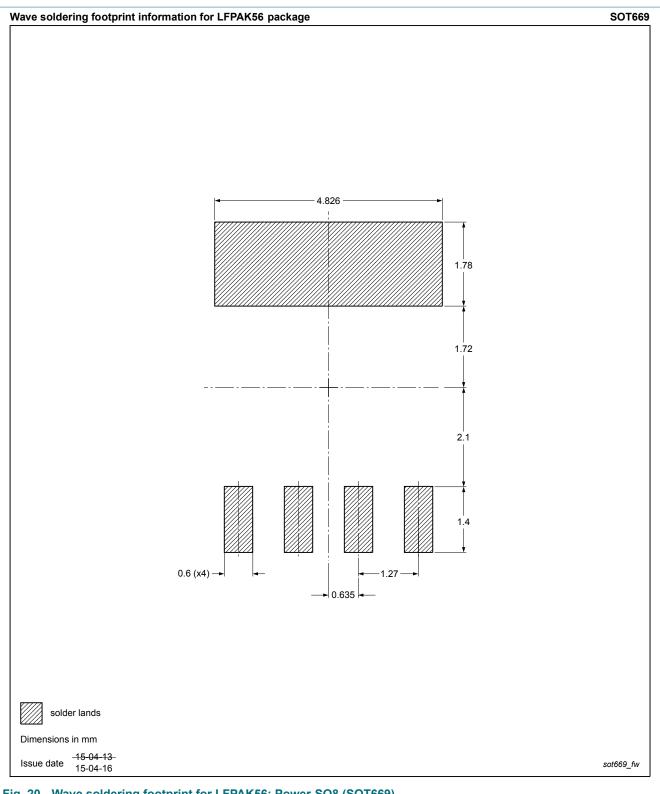


Fig. 20. Wave soldering footprint for LFPAK56; Power-SO8 (SOT669)

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